

SNx5C3232E 3V~5.5V、2チャンネルRS-232 1Mbit/s ライン・ドライバ/レシーバ、 ±15kV IEC ESD 保護機能搭載

1 特長

- 3V~5.5V の V_{CC} 電源で動作
- 最大 1Mbit/s で動作
- 低消費電流: ...300 μ A (標準値)
- 外付けコンデンサ ...4 \times 0.1 μ F
- 3.3V 電源で 5V ロジック入力を受容
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能
- RS-232 ピンの ESD 保護
 - \pm 15kV 人体モデル (HBM)
 - \pm 15kV IEC 61000-4-2 エアギャップ放電
 - \pm 8kV IEC 61000-4-2 接触放電

2 アプリケーション

- 産業用 PC
- 有線ネットワーク
- データ・センターおよびエンタープライズ・コンピューティング
- バッテリ駆動システム
- PDA
- ノートブック PC
- パームトップ PC
- ハンドヘルド機器

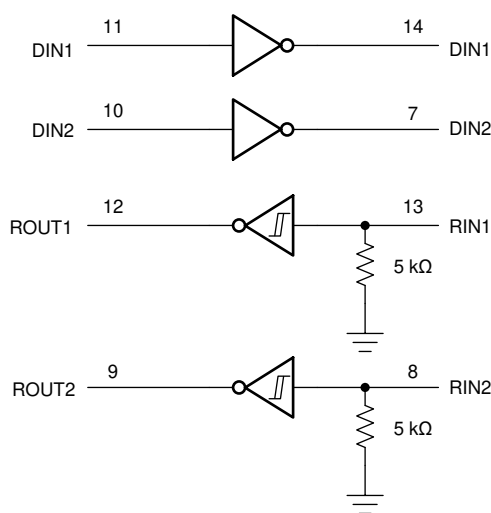
3 概要

SN65C3232E および SN75C3232E は 2 つのライン・ドライバ、2 つのライン・レシーバ、1 つのデュアル・チャージ・ポンプ回路で構成されており、 \pm 15kV のピン間 (シリアル・ポート接続ピン、GND を含む) ESD 保護機能を備えています。これらのデバイスは、非同期通信コントローラとシリアルポート・コネクタの間の電気的インターフェイスとして機能します。チャージ・ポンプと 4 つの小さな外付けコンデンサにより、3V~5.5V の単一電源で動作できます。本デバイスは最大 1Mbit/s (標準値) のデータ信号速度、14V/ μ s~150V/ μ s のドライバ出力スlewレイトで動作します。

製品情報

部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)
SN65C3232E SN75C3232E	D (SOIC)	9.90mm \times 3.91mm
	DB (SSOP)	6.20mm \times 5.30mm
	DW (SOIC)	10.3mm \times 7.50mm
	PW (TSSOP)	5.00mm \times 4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



論理図 (正論理)



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision A (December 2007) to Revision B (June 2021)	Page
• 「製品情報」表、「ピン構成および機能」セクション、「温度情報」表、「機能説明」セクション、「デバイスの機能モード」、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加。.....	1
• 「アプリケーション」の一覧を更新.....	1
• Added a note specifying a minimum capacitor of 1 μF between V_{CC} and GND to satisfy IEC ESD specifications in the <i>ESD Protection, Driver</i> table.....	4
• Added a note specifying the need for a 1- μF capacitor between V_{CC} and GND to satisfy IEC ESD specifications in the <i>ESD Protection, Receiver</i> table.....	4

5 Pin Configuration and Functions

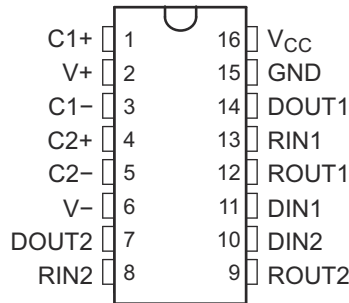


图 5-1. D, DB, DW, or PW Package (Top View)

表 5-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	D, DB, DW or PW		
C1+	1	-	Positive lead of C1 capacitor
V+	2	O	Positive charge pump output for storage capacitor only
C1-	3	-	Negative lead of C1 capacitor
C2+	4	-	Positive lead of C2 capacitor
C2-	5	-	Negative lead of C2 capacitor
V-	6	O	Negative charge pump output for storage capacitor only
DOUT2	7	O	RS232 line data output (to remote RS232 system)
RIN2	8	I	RS232 line data input (from remote RS232 system)
ROUT2	9	O	Logic data output (to UART)
DIN2	10	I	Logic data input (from UART)
DIN1	11	I	Logic data input (from UART)
ROUT1	12	O	Logic data output (to UART)
RIN1	13	I	RS232 line data input (from remote RS232 system)
DOUT1	14	O	RS232 line data output (to remote RS232 system)
GRD	15	-	Ground
V _{CC}	16	-	Supply Voltage, Connect to external 3-V to 5.5-V power supply
Thermal Pad	-	-	Exposed thermal pad. Can be connected to GND or left floating.

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) see ⁽¹⁾

		MIN	MAX	UNIT	
V _{CC}	Supply voltage range ⁽²⁾	-0.3	6	V	
V+	Positive output supply voltage range ⁽²⁾	-0.3	7	V	
V-	Negative output supply voltage range ⁽²⁾	0.3	-7	V	
V+ – V-	Supply voltage difference ⁽²⁾		13	V	
V _I	Input voltage range	Drivers	-0.3	6	V
		Receivers	-25	25	
V _O	Output voltage range	Drivers	-13.2	13.2	V
		Receivers	-0.3	V _{CC} + 0.3	
T _J	Operating virtual junction temperature		150	°C	
T _{stg}	Storage temperature range	-65	150	°C	

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) All voltages are with respect to network GND.

6.2 ESD Protection

		VALUE	UNIT	
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾ .	±3000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 ESD Protection, Driver

PIN		TEST CONDITIONS	TYP	UNIT
NAME	NO.			
DOUT	7, 14	HBM, per ANSI/ESDA/JEDEC JS-001	±15	kV
		IEC 61000-4-2 Air-Gap Discharge ⁽¹⁾	±15	
		IEC 61000-4-2 Contact Discharge ⁽¹⁾	±8	

- (1) For D, DB, PW packages of SN65C3232E and PW package of SN75C3232E: A minimum of 1-μF capacitor is needed between VCC and GND to meet the specified IEC ESD level

6.4 ESD Protection, Receiver

PIN		TEST CONDITIONS	TYP	UNIT
NAME	NO.			
RIN	8, 13	HBM, per ANSI/ESDA/JEDEC JS-001	±15	kV
		IEC 61000-4-2 Air-Gap Discharge ⁽¹⁾	±15	
		IEC 61000-4-2 Contact Discharge ⁽¹⁾	±8	

- (1) For D, DB, PW packages of SN65C3232E and PW package of SN75C3232E: A minimum of 1-μF capacitor is needed between VCC and GND to meet the specified IEC ESD level

6.5 Recommended Operating Conditions

see note (1)

			MIN	NOM	MAX	UNIT
Supply voltage		$V_{CC} = 3.3\text{ V}$	3	3.3	3.6	V
		$V_{CC} = 5\text{ V}$	4.5	5	5.5	
V_{IH}	Driver high-level input voltage	DIN	$V_{CC} = 3.3\text{ V}$		2	V
			$V_{CC} = 5\text{ V}$		2.4	
V_{IL}	Driver low-level input voltage	DIN			0.8	V
V_I	Driver input voltage	DIN			0	V
	Receiver input voltage				–25	
T_A	Operating free-air temperature	SN65C3232E			–40	°C
		SN75C3232E			0	

(1) Test conditions are $C1-C4 = 0.1\ \mu\text{F}$ at $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$; $C1 = 0.047\ \mu\text{F}$, $C2-C4 = 0.33\ \mu\text{F}$ at $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$ (see [9-1](#)).

6.6 Thermal Information, SN65C3232E

THERMAL METRIC ⁽¹⁾		SN65C3232E				UNIT
		PW (TSSOP)	D (SOIC)	DW (SOIC)	DB (SSOP)	
		16 Pins	16 Pins	16 Pins	16 Pins	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	108.0	85.9	57.0	103.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	39.0	43.1	33.5	49.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54.4	44.5	37.1	54.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	3.3	10.1	7.5	12.0	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	53.8	44.1	37.1	54.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

6.7 Thermal Information, SN75C3232E

THERMAL METRIC ⁽¹⁾		SN75C3232E				UNIT
		PW (TSSOP)	D (SOIC)	DW (SOIC)	DB (SSOP)	
		16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	108.0	82.0	57.0	46.0	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	39.0	36.7	33.5	36.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	54.4	33.6	37.1	43.8	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	3.3	4.2	7.5	4.2	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	53.8	33.3	37.1	42.9	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

6.8 Electrical Characteristics, Power

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽²⁾	MIN	TYP ⁽¹⁾	MAX	UNIT
I_{CC}	Supply current	No load, $V_{CC} = 3.3 \text{ V or } 5 \text{ V}$		0.3	1	mA

(1) All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^\circ\text{C}$.

(2) Test conditions are C1–C4 = 0.1 μF at $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$; C1 = 0.047 μF , C2–C4 = 0.33 μF at $V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$ (see [9-1](#)).

6.9 Electrical Characteristics, Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽³⁾	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND, DIN = GND	5	5.5		V
V_{OL}	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND, DIN = V_{CC}	–5	–5.4		V
I_{IH}	High-level input current	$V_I = V_{CC}$		± 0.01	± 1	μA
I_{IL}	Low-level input current	V_I at GND		± 0.01	± 1	μA
I_{OS} (2)	Short-circuit output current	$V_{CC} = 3.6 \text{ V}$, $V_O = 0 \text{ V}$		± 35	± 60	mA
		$V_{CC} = 5.5 \text{ V}$, $V_O = 0 \text{ V}$		± 35	± 90	
r_o	Output resistance	V_{CC} , $V+$, and $V- = 0 \text{ V}$, $V_O = \pm 2 \text{ V}$	300	10M		Ω

(1) All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^\circ\text{C}$.

(2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

(3) Test conditions are C1–C4 = 0.1 μF at $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$; C1 = 0.047 μF , C2–C4 = 0.33 μF at $V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$ (see [9-1](#)).

6.10 Electrical Characteristics, Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽²⁾	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{OH}	High-level output voltage	$I_{OH} = -1 \text{ mA}$	$V_{CC} - 0.6$	$V_{CC} - 0.1$		V
V_{OL}	Low-level output voltage	$I_{OL} = 1.6 \text{ mA}$			0.4	V
V_{IT+}	Positive-going input threshold voltage	$V_{CC} = 3.3 \text{ V}$		1.5	2.4	V
		$V_{CC} = 5 \text{ V}$		1.8	2.4	
V_{IT-}	Negative-going input threshold voltage	$V_{CC} = 3.3 \text{ V}$	0.6	1.2		V
		$V_{CC} = 5 \text{ V}$	0.8	1.5		
V_{hys}	Input hysteresis ($V_{IT+} - V_{IT-}$)			0.3		V
r_i	Input resistance	$V_I = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	k Ω

(1) All typical values are at $V_{CC} = 3.3 \text{ V}$ or $V_{CC} = 5 \text{ V}$, and $T_A = 25^\circ\text{C}$.

(2) Test conditions are C1–C4 = 0.1 μF at $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$; C1 = 0.047 μF , C2–C4 = 0.33 μF at $V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$ (see [9-1](#)).

6.11 Switching Characteristics, Driver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽³⁾		MIN	TYP ⁽¹⁾	MAX	UNIT
Maximum data rate (see 7-1)	R _L = 3 kΩ, One DOUT switching	C _L = 250 pF, V _{CC} = 3 V to 4.5 V		1000			kbit/s
		C _L = 1000 pF, V _{CC} = 3.5 V to 5.5 V		1000			
t _{sk(p)}	Pulse skew ⁽²⁾	C _L = 150 pF to 2500 pF, R _L = 3 kΩ to 7 kΩ, See 7-2			300		ns
SR(tr)	Slew rate, transition region (see 7-1)	R _L = 3 kΩ to 7 kΩ, C _L = 150 pF to 1000 pF, V _{CC} = 3.3 V			14	150	V/μs

- (1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
- (2) Pulse skew is defined as |t_{PLH} – t_{PHL}| of each channel of the same device.
- (3) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V (see [9-1](#)).

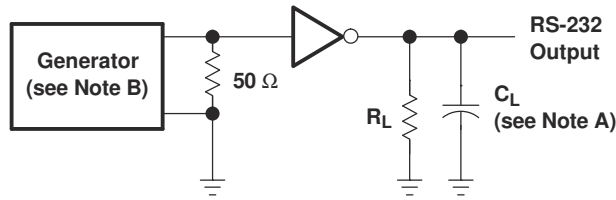
6.12 Switching Characteristics, Receiver

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS ⁽³⁾	TYP ⁽¹⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C _L = 150 pF	300	ns
t _{PHL}	Propagation delay time, high- to low-level output		300	ns
t _{sk(p)}	Pulse skew ⁽²⁾		300	ns

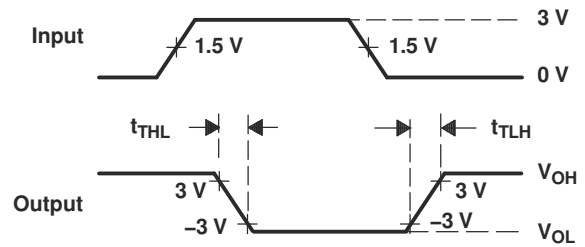
- (1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
- (2) Pulse skew is defined as |t_{PLH} – t_{PHL}| of each channel of the same device.
- (3) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V (see [9-1](#)).

7 Parameter Measurement Information



TEST CIRCUIT

$$SR(tr) = \frac{6\text{ V}}{t_{THL} \text{ or } t_{TLH}}$$

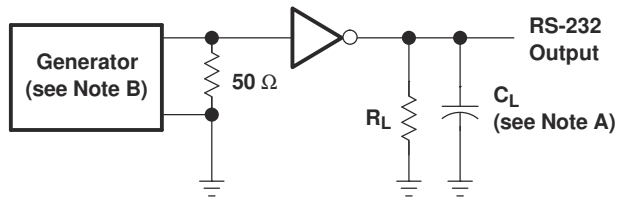


VOLTAGE WAVEFORMS

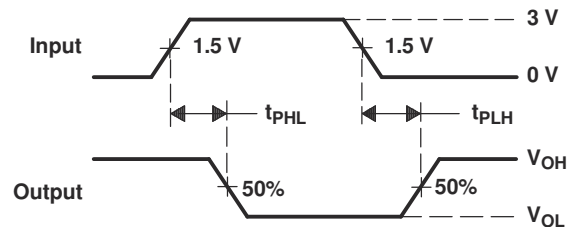
NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

7-1. Driver Slew Rate



TEST CIRCUIT

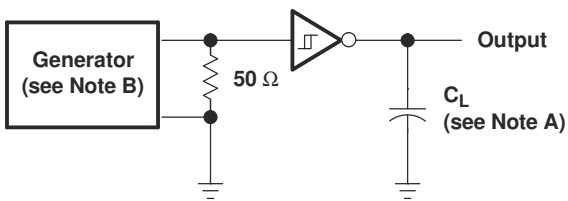


VOLTAGE WAVEFORMS

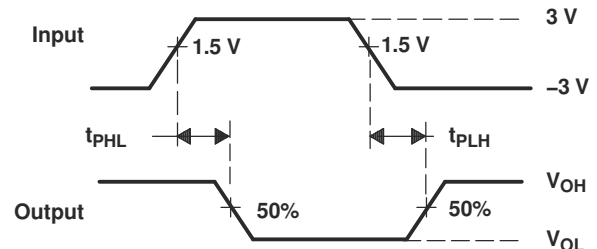
NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

7-2. Driver Pulse Skew



TEST CIRCUIT



VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: $Z_O = 50\ \Omega$, 50% duty cycle, $t_r \leq 10\text{ ns}$, $t_f \leq 10\text{ ns}$.

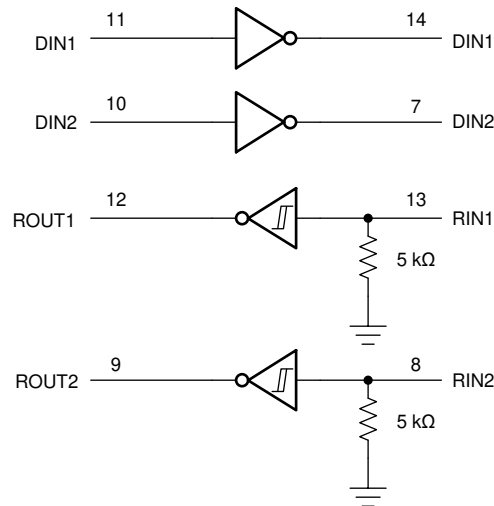
7-3. Receiver Propagation Delay Times

8 Detailed Description

8.1 Overview

The SNx5C3232E device consists of two line drivers, two line receivers, and a dual charge-pump circuit with ± 15 -kV IEC ESD protection between serial-port connection terminals and GND. The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from one 3-V to 5.5-V supply. The device operates at data signaling rates up to 1 Mbps and a maximum of 150-V/ μ s driver output slew rate. Outputs are protected against shorts to ground.

8.1.1 Functional Block Diagram



8.1.2 Feature Description

8.1.2.1 Power

The power block increases, inverts, and regulates voltage at V+ and V– pins using a charge pump that requires four external capacitors.

8.1.2.2 RS232 Driver

Two drivers interface the standard logic level to RS232 levels. Both DIN inputs must be valid high or low.

8.1.2.3 RS232 Receiver

Two receivers interface RS232 levels to standard logic levels. An open input results in a high output on ROUT. Each RIN input includes an internal standard RS232 load.

8.1.3 Device Functional Modes

表 8-1. Each Driver

INPUT DIN ⁽¹⁾	OUTPUT DOUT
L	H
H	L

(1) H = high level, L = low level

表 8-2. Each Receiver

INPUT RIN ⁽¹⁾	OUTPUT ROUT
L	H
H	L
Open	H

(1) H = high level, L = low level,
Open = input disconnected or connected driver off

8.1.3.1 V_{CC} Powered by 3 V to 5.5 V

The device is in normal operation.

8.1.3.2 V_{CC} Unpowered, $V_{CC} = 0 V$

When the SNx5C3232E device is unpowered, it can be safely connected to an active remote RS232 device.

9 Application and Implementation

Note

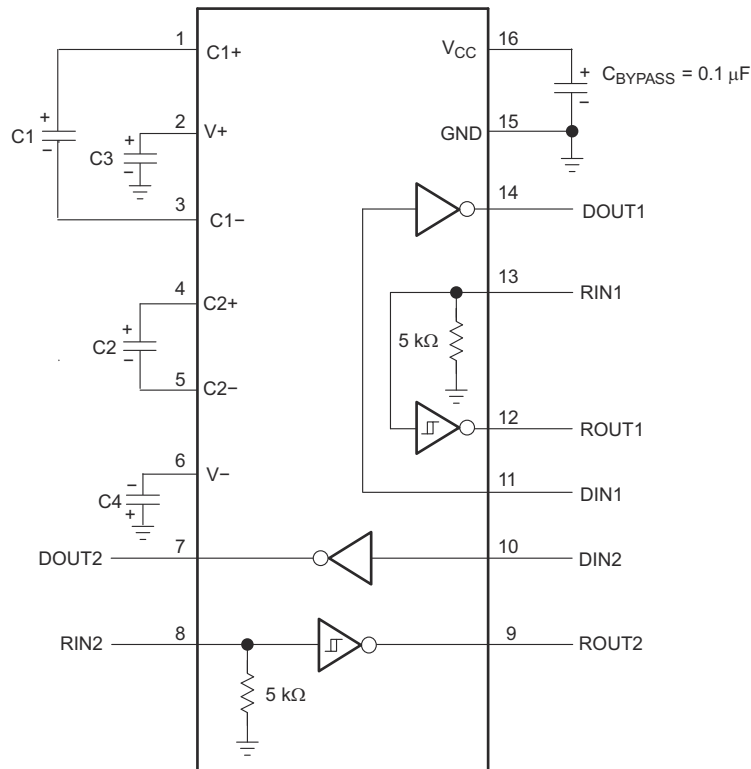
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SNx5C3232E device is designed to convert single-ended signals into RS232-compatible signals, and vice-versa. This device can be used in any application where an RS232 line driver or receiver is required.

ROUT and DIN connect to UART or general-purpose logic lines. RIN and DOUT lines connect to a RS232 connector or cable.

Typical Application



A. C3 can be connected to V_{CC} or GND.

图 9-1. Typical Operating Circuit and Capacitor Values

表 9-1. V_{CC} vs Capacitor Values

V_{CC}	C1	C2, C3, C4
3.3 V \pm 0.3 V	0.1 μ F	0.1 μ F
5 V \pm 0.5 V	0.047 μ F	0.33 μ F
3 V to 5.5 V	0.1 μ F	0.47 μ F

9.2.1 Design Requirements

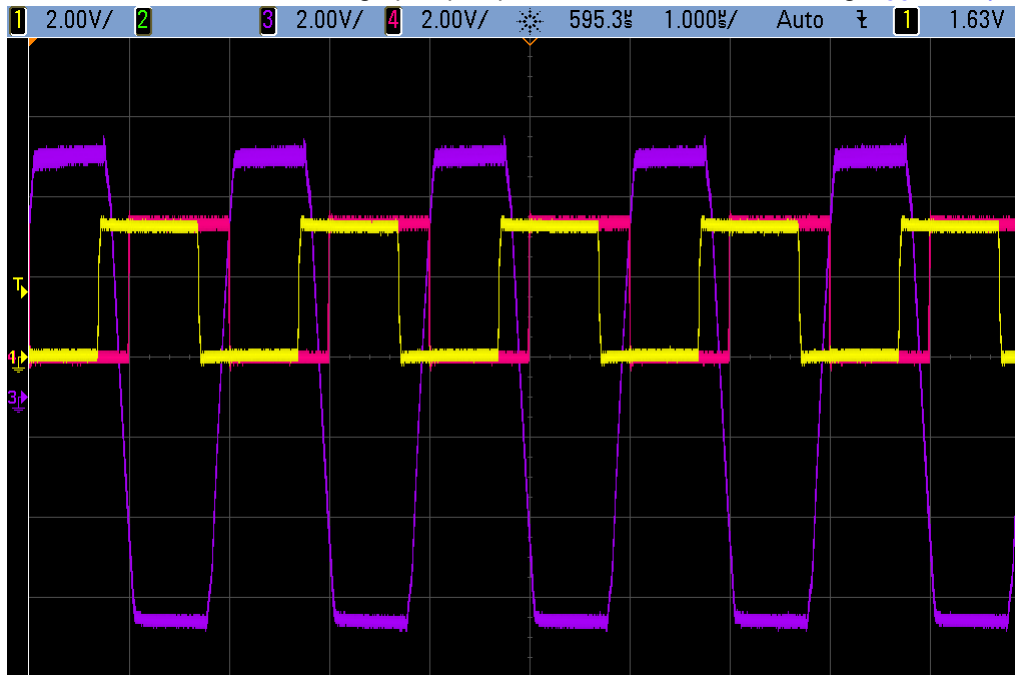
- Recommended V_{CC} is 3.3 V or 5 V
 - 3 V to 5.5 V is also possible
- Maximum recommended bit rate is 1 Mbps

9.2.2 Detailed Design Procedure

All DIN inputs must be connected to valid low or high logic levels. Select capacitor values based on V_{CC} level for best performance.

9.2.3 Application Performance Plots

V_{CC} must be between 3 V and 5.5 V. Charge pump capacitors must be chosen using [V_{CC} vs Capacitor Values](#)



9-2. 1 Mbps timing waveform from driver input to receiver output loopback. DOUT to RIN trace is in purple, DIN trace is in yellow and ROUT trace is in pink

10 Power Supply Recommendations

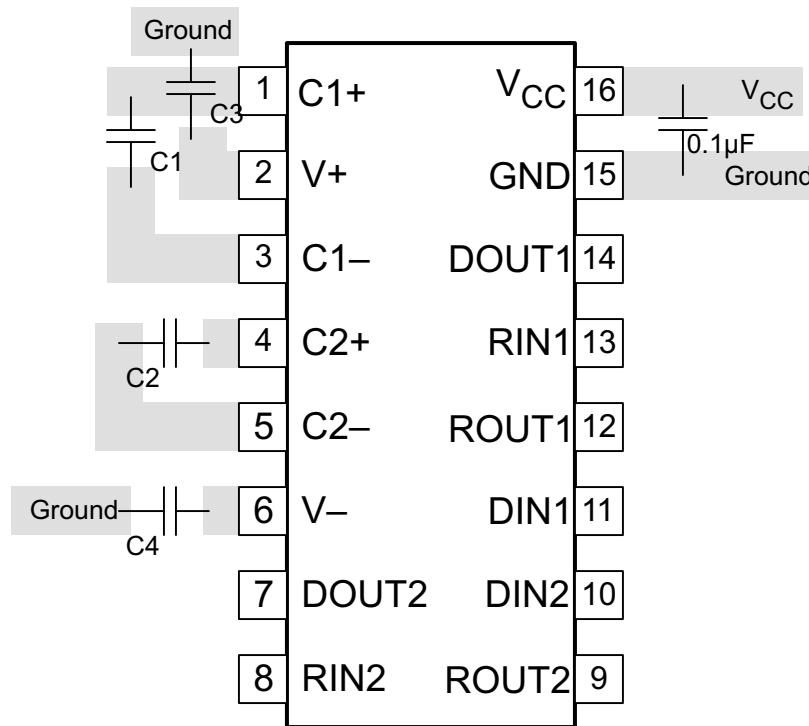
The supply voltage, V_{CC} , should be between 3 V and 5.5 V. Select the charge-pump capacitors using [V_{CC} vs Capacitor Values](#).

11 Layout

11.1 Layout Guidelines

Keep the external capacitor traces short, specifically on the C1 and C2 nodes that have the fastest rise and fall times.

11.2 Layout Example



✎ 11-1. Layout Diagram

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 サポート・リソース

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12.3 Trademarks

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12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C3232EDBR	ACTIVE	SSOP	DB	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDBRG4	ACTIVE	SSOP	DB	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN65C3232EDR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDRG4	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDW	ACTIVE	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EDWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3232E	Samples
SN65C3232EPWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU232E	Samples
SN75C3232EDW	ACTIVE	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	Samples
SN75C3232EDWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	75C3232E	Samples
SN75C3232EPWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	MY232E	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3232EDBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN65C3232EDBR	SSOP	DB	16	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN65C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65C3232EDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN65C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN65C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN75C3232EDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN75C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN75C3232EPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3232EDBR	SSOP	DB	16	2000	356.0	356.0	35.0
SN65C3232EDBR	SSOP	DB	16	2000	356.0	356.0	35.0
SN65C3232EDR	SOIC	D	16	2500	356.0	356.0	35.0
SN65C3232EDR	SOIC	D	16	2500	356.0	356.0	35.0
SN65C3232EDWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN65C3232EPWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN75C3232EDWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN75C3232EPWR	TSSOP	PW	16	2000	356.0	356.0	35.0
SN75C3232EPWR	TSSOP	PW	16	2000	356.0	356.0	35.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65C3232EDW	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN75C3232EDW	DW	SOIC	16	40	506.98	12.7	4826	6.6

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
 - E. Reference JEDEC MS-012 variation AC.



4220204/A 02/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220204/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

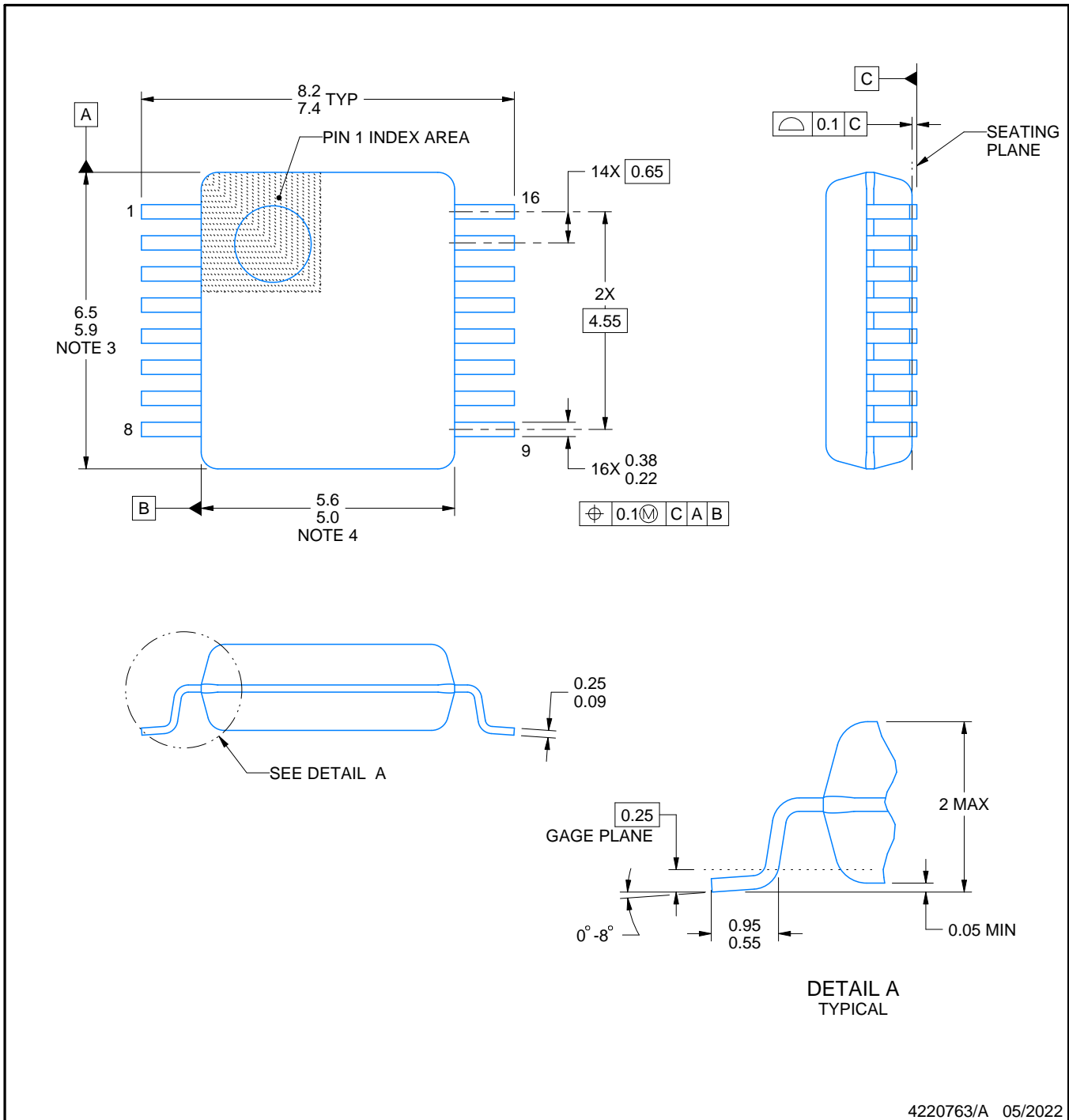
DB0016A



PACKAGE OUTLINE

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



4220763/A 05/2022

NOTES:

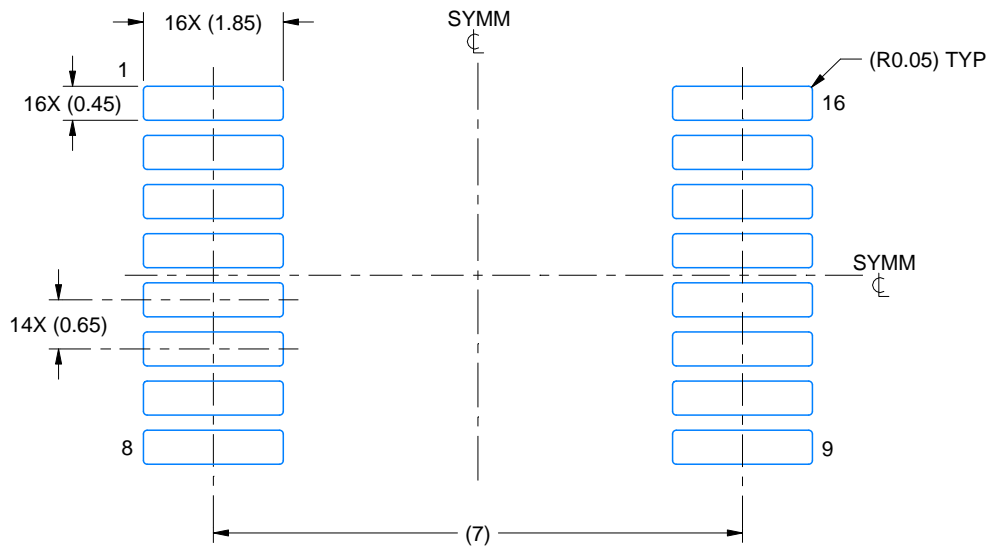
- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- This drawing is subject to change without notice.
- This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
- Reference JEDEC registration MO-150.

EXAMPLE BOARD LAYOUT

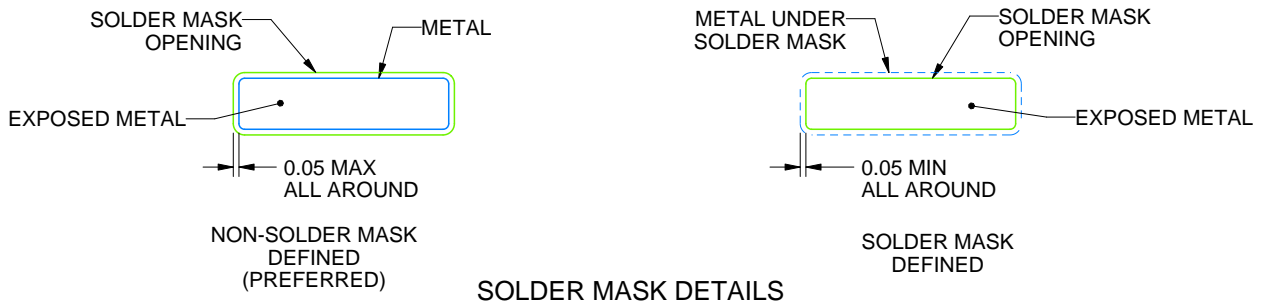
DB0016A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220763/A 05/2022

NOTES: (continued)

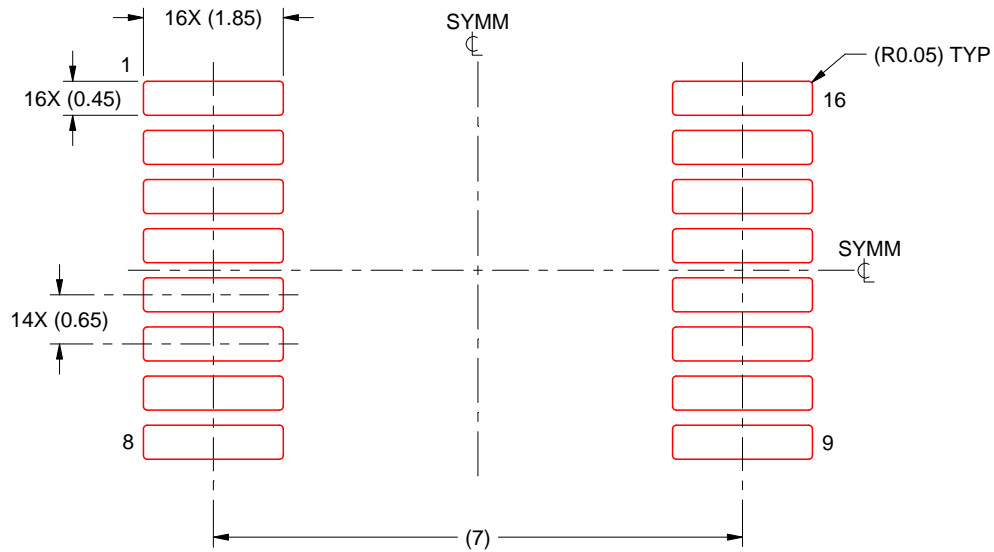
- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DB0016A

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220763/A 05/2022

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

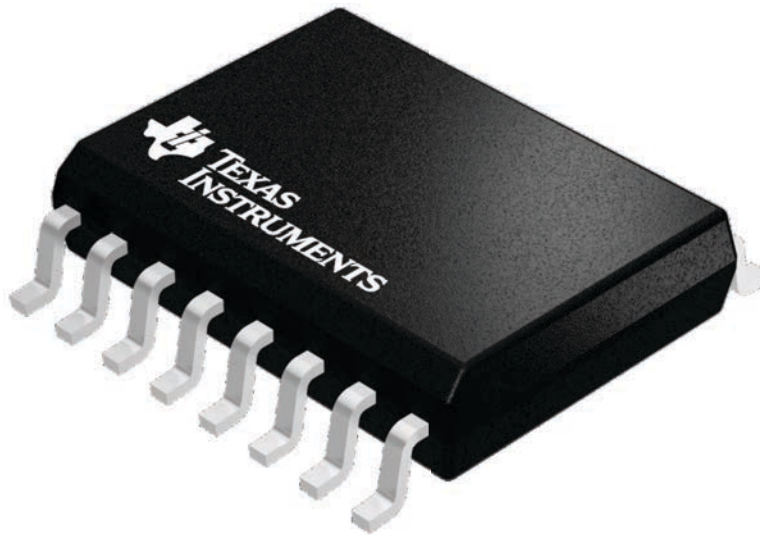
DW 16

SOIC - 2.65 mm max height

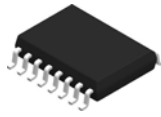
7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224780/A

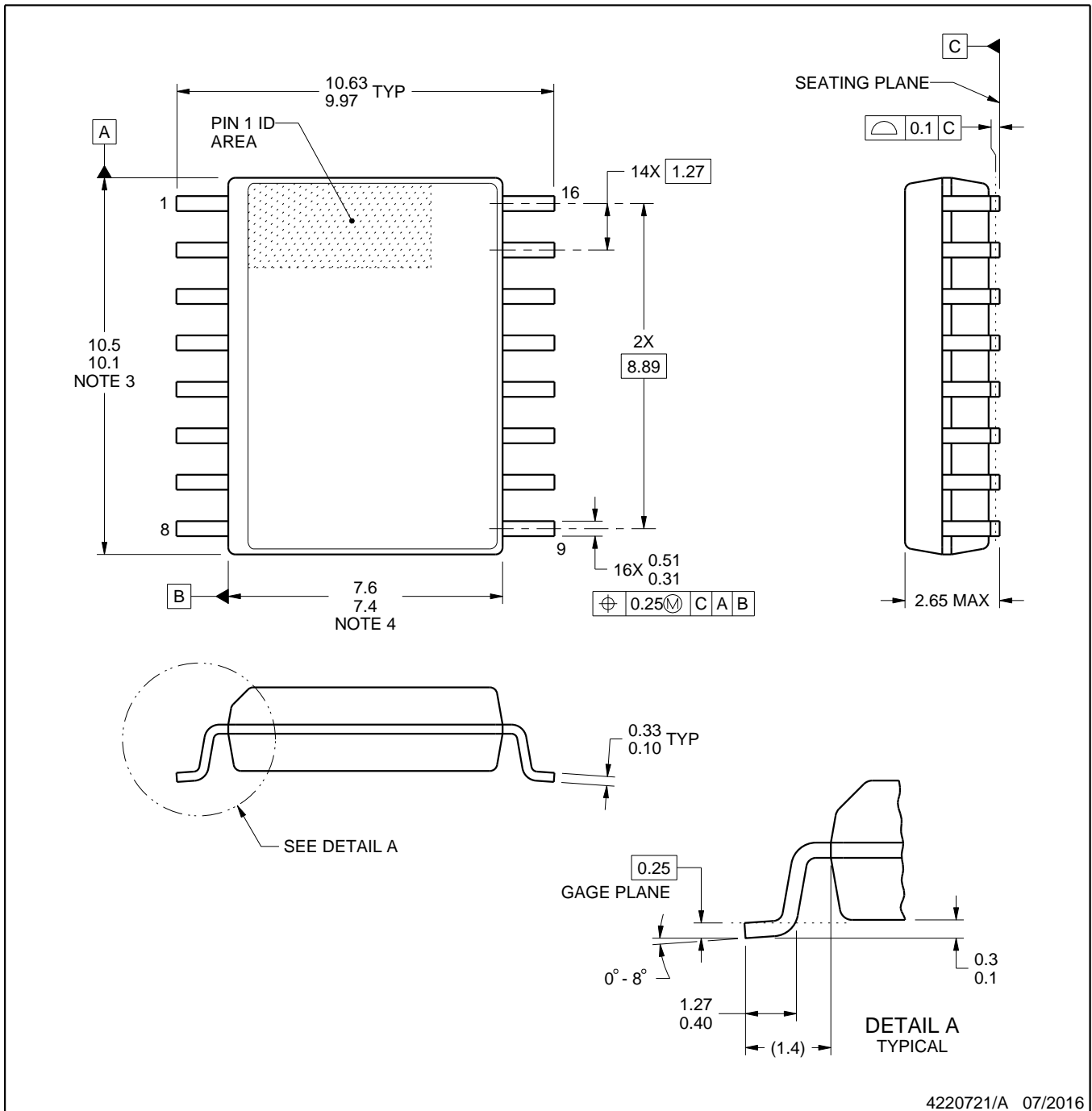


DW0016A

PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



4220721/A 07/2016

NOTES:

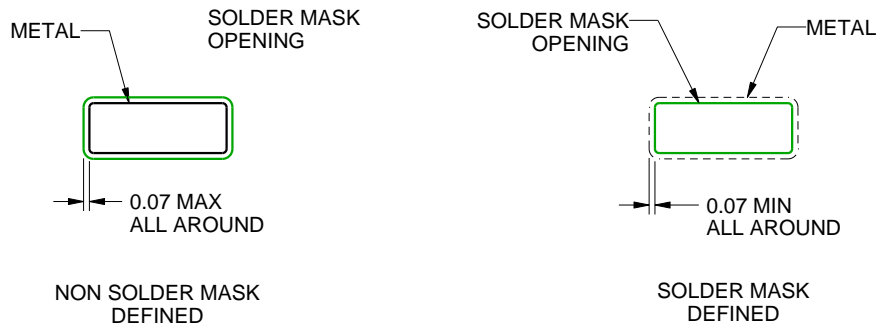
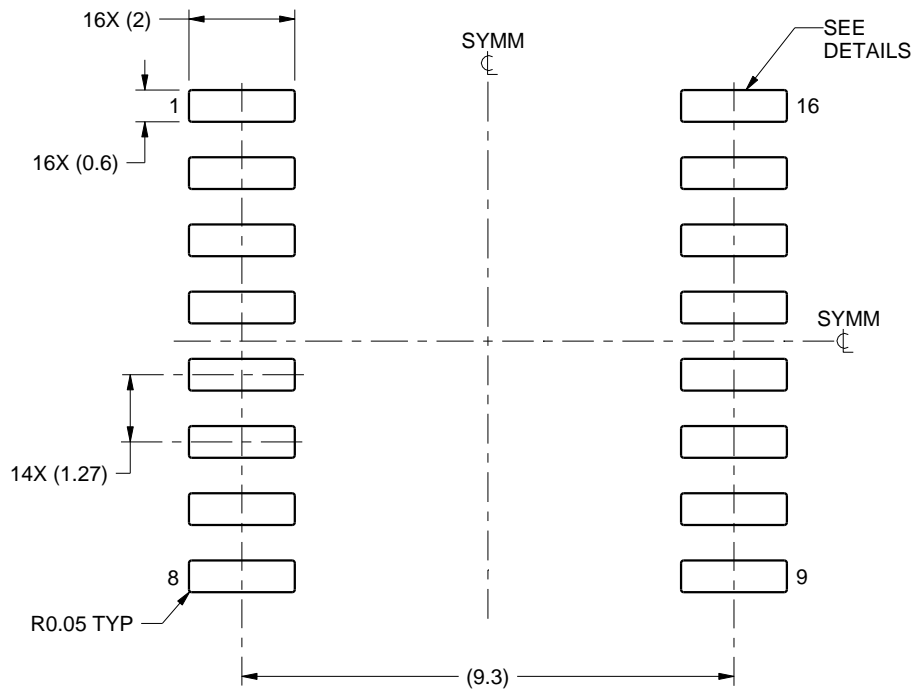
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DW0016A

SOIC - 2.65 mm max height

SOIC



SOLDER MASK DETAILS

4220721/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

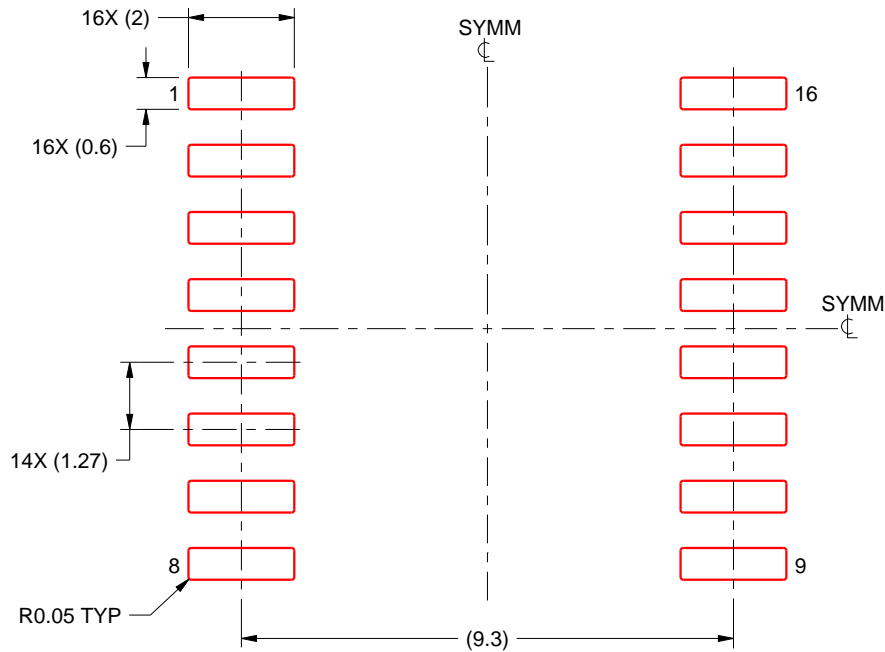
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0016A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220721/A 07/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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